

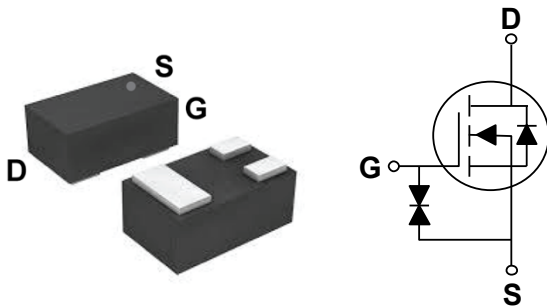


General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BV_{DSS}	R_{DS(ON)}	I_D
20 V	350 mΩ	500 mA

SOT-883 Pin Configuration



Features

- R_{DS(ON)} = ≤ 350mΩ@V_{GS}=4.5V
- Fast switching
- Green Device Available
- Suit for 1.2V Gate Drive Applications
- 2KV HBM ESD Capability

Applications

- Notebook
- Smartphone
- Battery Protection
- Hand-Held Instrument

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±8	V
I _D	Drain Current - Continuous (T _C =25°C)	500	mA
	Drain Current - Continuous (T _C =100°C)	320	mA
I _{DM}	Drain Current - Pulsed (NOTE 1)	1000	mA
P _D	Power Dissipation (T _C =25°C)	155	mW
	Power Dissipation - Derate above 25°C	1.25	mW/°C
T _J	Operating Junction Temperature Range	-50 to 150	°C
T _{STG}	Storage Temperature Range	-50 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to Ambient	---	800	°C/W



Electrical Characteristics (T_J=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =20V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =16V, V _{GS} =0V, T _J =125°C	---	---	10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±8V, V _{DS} =0V	---	---	±20	uA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =4.5V, I _D =0.5A	---	200	350	mΩ
		V _{GS} =2.5V, I _D =0.4A	---	235	450	
		V _{GS} =1.8V, I _D =0.2A	---	295	600	
		V _{GS} =1.5V, I _D =0.1A	---	365	800	
		V _{GS} =1.2V, I _D =0.1A	---	600	1500	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.3	0.5	0.8	V

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q _g	Total Gate Charge (NOTE 2、3)	V _{DS} =10V, V _{GS} =4.5V, I _D =0.5A	---	1	2	nC
Q _{gs}	Gate-Source Charge (NOTE 2、3)		---	0.26	0.5	
Q _{gd}	Gate-Drain Charge (NOTE 2、3)		---	0.2	0.4	
T _{d(on)}	Turn-On Delay Time (NOTE 2、3)	V _{DD} =10V, V _{GS} =4.5V, R _G =10Ω, I _D =0.5A	---	5	10	nS
T _r	Rise Time (NOTE 2、3)		---	3.5	7	
T _{d(off)}	Turn-Off Delay Time (NOTE 2、3)		---	14	28	
T _f	Fall Time (NOTE 2、3)		---	6	12	
C _{ISS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, F=1MHz	---	38.2	75	pF
C _{OSS}	Output Capacitance		---	14.4	28	
C _{rSS}	Reverse Transfer Capacitance		---	6	12	

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	500	mA
I _{SM}	Pulsed Source Current		---	---	1000	mA
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =0.2A, T _J =25°C	---	---	1	V

NOTES :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
3. Essentially independent of operating temperature.



Characteristics Curves

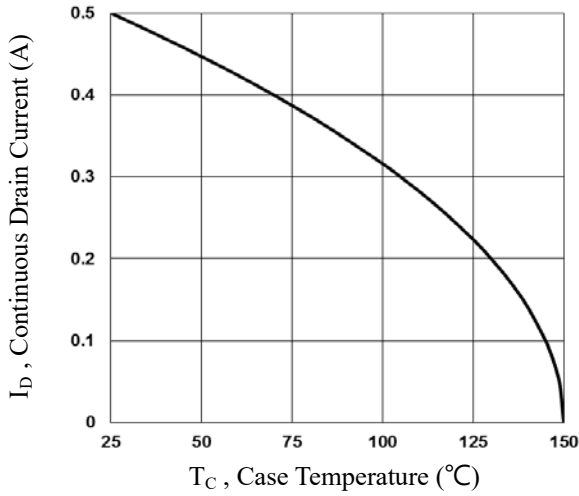


Fig.1 Continuous Drain Current vs. T_C

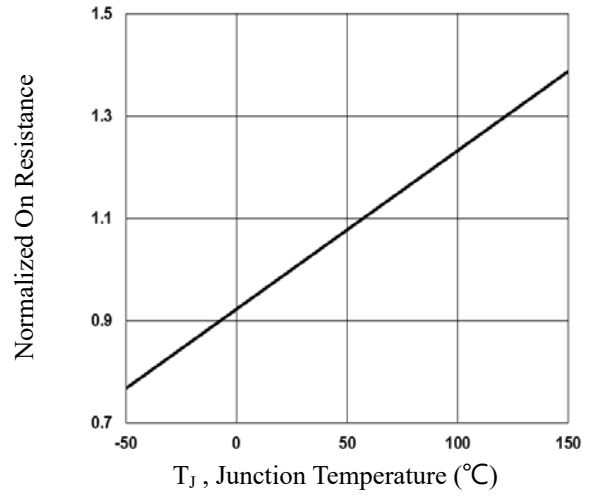


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

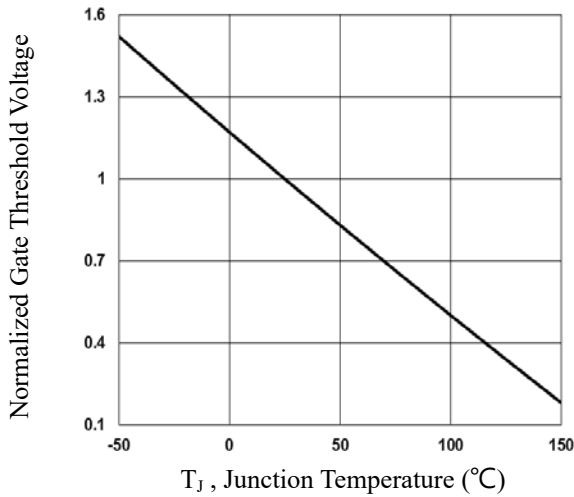


Fig.3 Normalized V_{th} vs. T_J

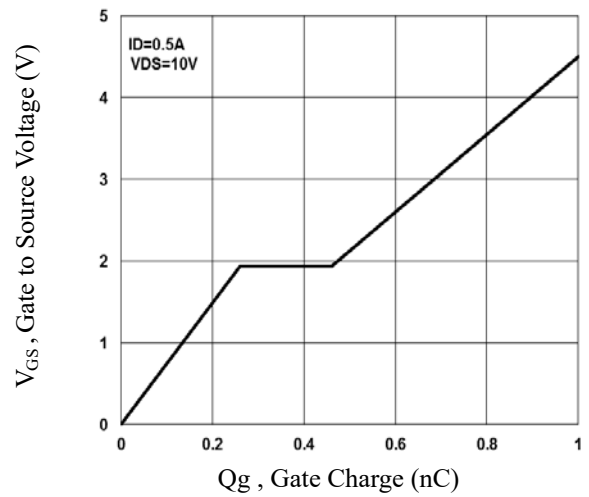


Fig.4 Gate Charge Waveform

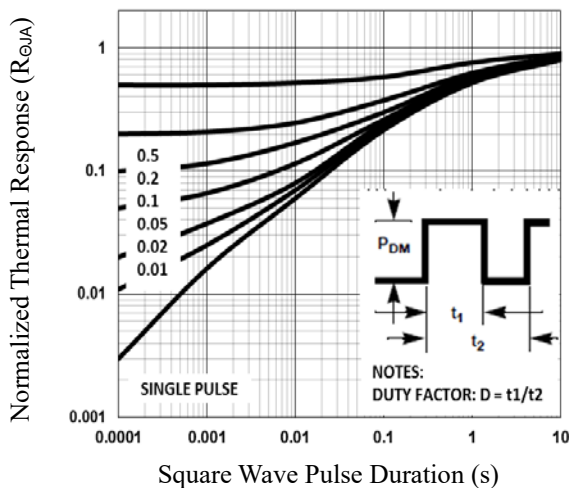


Fig.5 Normalized Transient Response

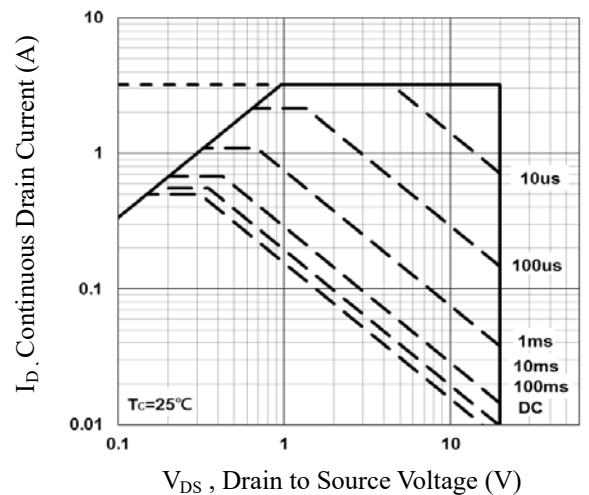


Fig.6 Maximum Safe Operation Area



Characteristics Curves

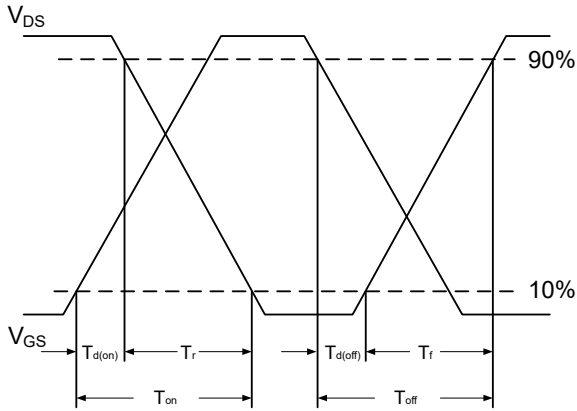


Fig.7 Switching Time Waveform

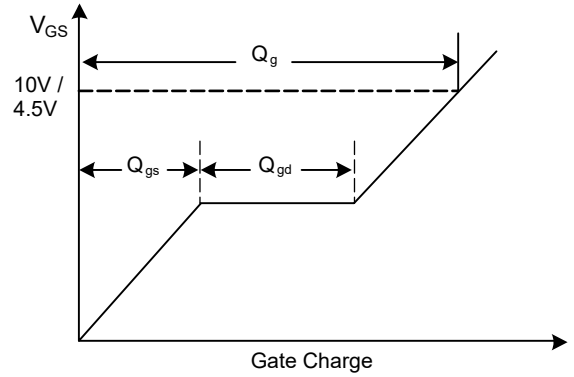
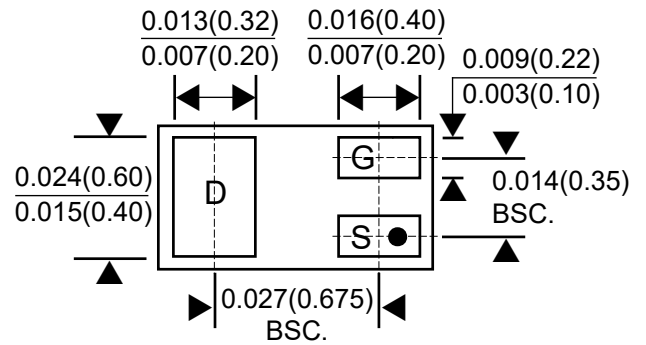
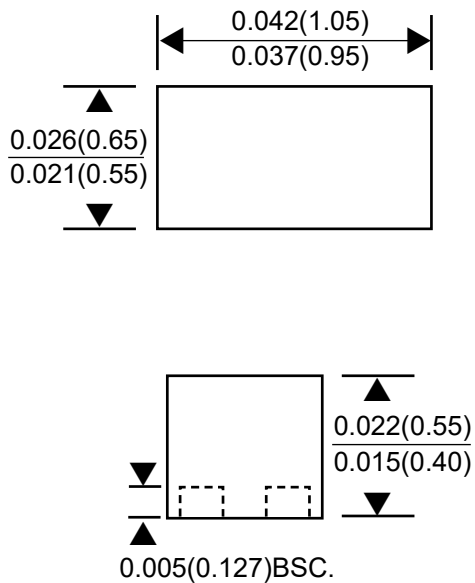


Fig.8 Gate Charge Waveform

Package Outline Dimensions



SOT-883

Dimensions in inches and (millimeters)



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